

2N3055(NPN), MJ2955(PNP)

2N3055D 供应商

Preferred Device

Complementary Silicon Power Transistors

Complementary silicon power transistors are designed for general-purpose switching and amplifier applications.

Features

- DC Current Gain – $h_{FE} = 20-70 @ I_C = 4 \text{ A dc}$
- Collector–Emitter Saturation Voltage – $V_{CE(sat)} = 1.1 \text{ Vdc (Max) @ } I_C = 4 \text{ A dc}$
- Excellent Safe Operating Area
- Pb–Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	60	Vdc
Collector–Emitter Voltage	V_{CER}	70	Vdc
Collector–Base Voltage	V_{CB}	100	Vdc
Emitter–Base Voltage	V_{EB}	7	Vdc
Collector Current – Continuous	I_C	15	A dc
Base Current	I_B	7	A dc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate Above 25°C	P_D	115 0.657	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +200	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

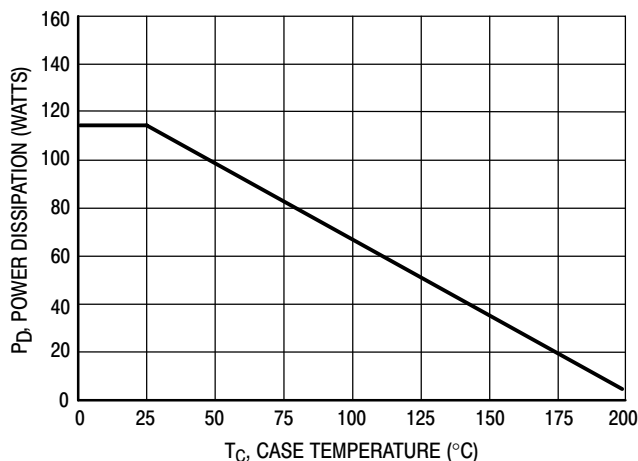


Figure 1. Power Derating

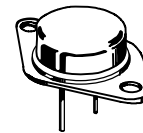
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

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**15 AMPERE
POWER TRANSISTORS
COMPLEMENTARY SILICON
60 VOLTS, 115 WATTS**



TO-204AA (TO-3)
CASE 1-07
STYLE 1

MARKING DIAGRAM



xxxx55 = Device Code
xxxx = 2N30 or MJ20
G = Pb–Free Package
A = Location Code
YY = Year
WW = Work Week
MEX = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
2N3055	TO–204AA	100 Units / Tray
2N3055G	TO–204AA (Pb–Free)	100 Units / Tray
MJ2955	TO–204AA	100 Units / Tray
MJ2955G	TO–204AA (Pb–Free)	100 Units / Tray

Preferred devices are recommended choices for future use and best overall value.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.52	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS*

Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 200\text{ mA dc}$, $I_B = 0$)	$V_{CEO(sus)}$	60	–	Vdc
Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 200\text{ mA dc}$, $R_{BE} = 100\ \Omega$)	$V_{CER(sus)}$	70	–	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$)	I_{CEO}	–	0.7	mA dc
Collector Cutoff Current ($V_{CE} = 100\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 100\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 150^{\circ}\text{C}$)	I_{CEX}	–	1.0 5.0	mA dc
Emitter Cutoff Current ($V_{BE} = 7.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	5.0	mA dc

ON CHARACTERISTICS* (Note 1)

DC Current Gain ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 10\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	h_{FE}	20 5.0	70 –	–
Collector-Emitter Saturation Voltage ($I_C = 4.0\text{ Adc}$, $I_B = 400\text{ mA dc}$) ($I_C = 10\text{ Adc}$, $I_B = 3.3\text{ Adc}$)	$V_{CE(sat)}$	–	1.1 3.0	Vdc
Base-Emitter On Voltage ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.5	Vdc

SECOND BREAKDOWN

Second Breakdown Collector Current with Base Forward Biased ($V_{CE} = 40\text{ Vdc}$, $t = 1.0\text{ s}$, Nonrepetitive)	$I_{s/b}$	2.87	–	Adc
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DYNAMIC CHARACTERISTICS

Current Gain – Bandwidth Product ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ MHz}$)	f_T	2.5	–	MHz
*Small-Signal Current Gain ($I_C = 1.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	15	120	–
*Small-Signal Current Gain Cutoff Frequency ($V_{CE} = 4.0\text{ Vdc}$, $I_C = 1.0\text{ Adc}$, $f = 1.0\text{ kHz}$)	f_{hfe}	10	–	kHz

*Indicates Within JEDEC Registration. (2N3055)

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

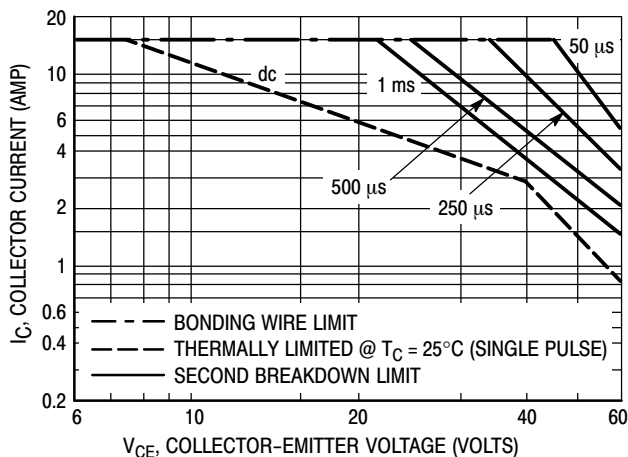


Figure 2. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_C = 25^{\circ}\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

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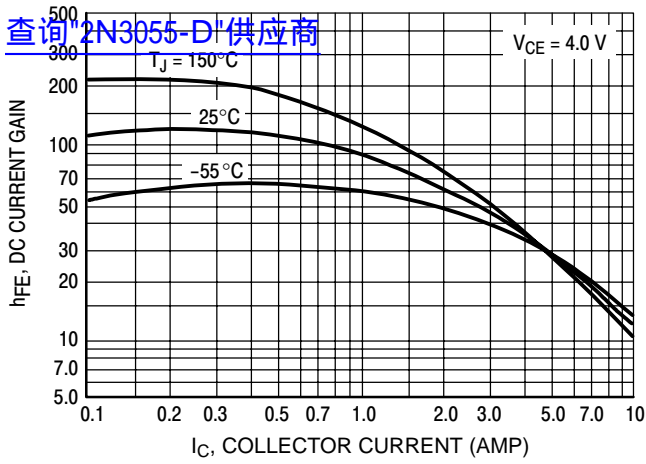


Figure 3. DC Current Gain, 2N3055 (NPN)

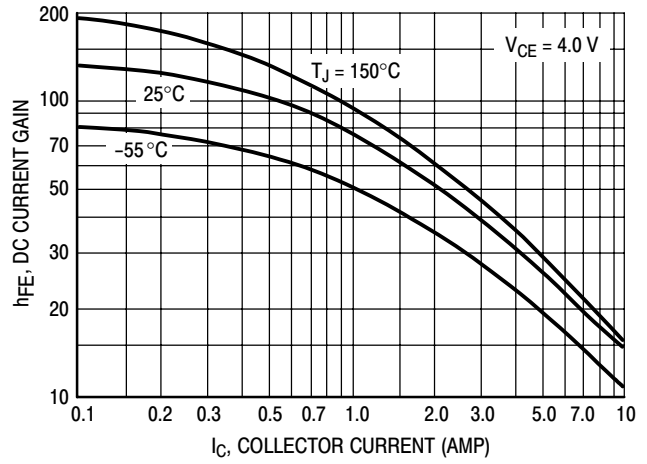


Figure 4. DC Current Gain, MJ2955 (PNP)

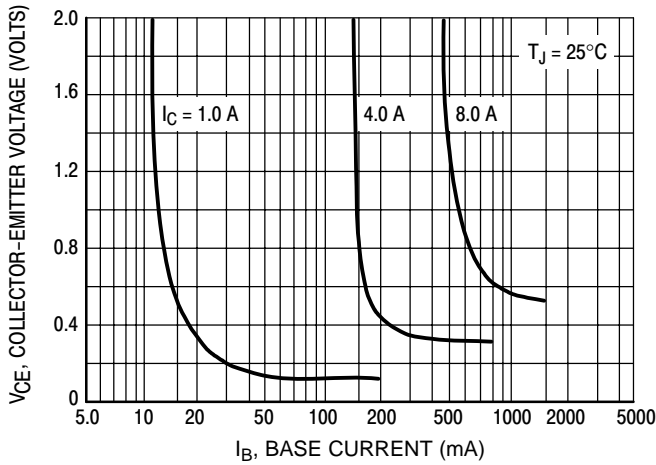


Figure 5. Collector Saturation Region, 2N3055 (NPN)

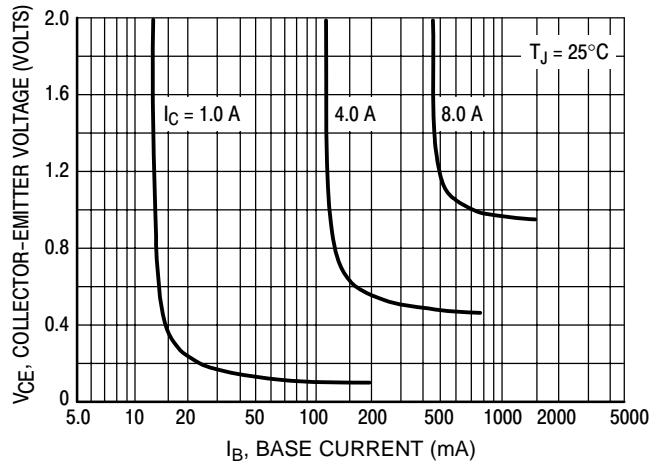


Figure 6. Collector Saturation Region, MJ2955 (PNP)

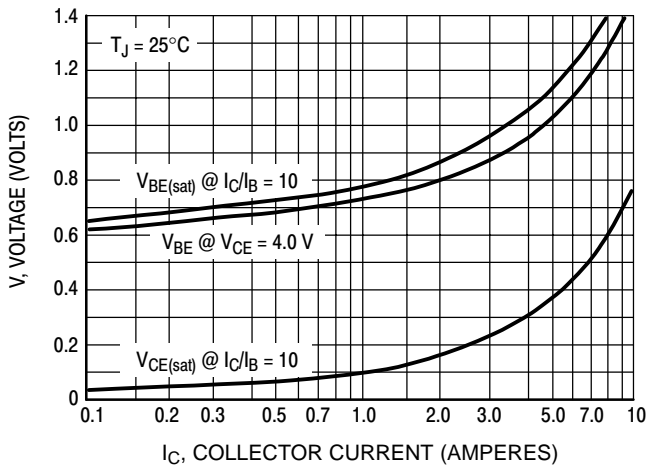


Figure 7. "On" Voltages, 2N3055 (NPN)

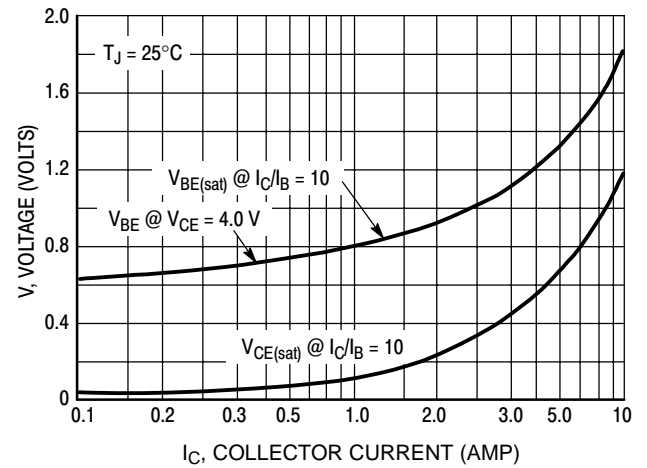


Figure 8. "On" Voltages, MJ2955 (PNP)

